



Docket No.: 50090-275

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

: **RESPONSE UNDER 37 CFR 1.116**  
: **EXPEDITED PROCEDURE**

Hiroki SHINKAWATA

Serial No.: 09/766,846

: Group Art Unit: 2811

Filed: January 23, 2001

: Examiner: Hung K. Vu

For: SEMICONDUCTOR DEVICE WITH TRANSFER GATE HAVING GATE  
INSULATING FILM AND GATE ELECTRODE LAYER

**AMENDMENT UNDER 37 CFR §1.116**

Box AF  
Commissioner for Patents  
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated July 26, 2002, pursuant to the provisions of 37 C.F.R. §1.116.

**IN THE CLAIMS:**

Please amend claims 1, 2, 9, 13 and 15 as follows.

1. (Amended) A semiconductor device, comprising:

conductive transfer gates;

contact plugs adjacent to said conductive transfer gates, each contact plug and each

conductive transfer gate having a respective upper surface, wherein the upper surfaces of the

contact plugs and the upper surfaces of the conductive transfer gates are substantially coplanar;

said each conductive transfer gate having a gate insulating film,

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